

Silicon PNP Power Transistors

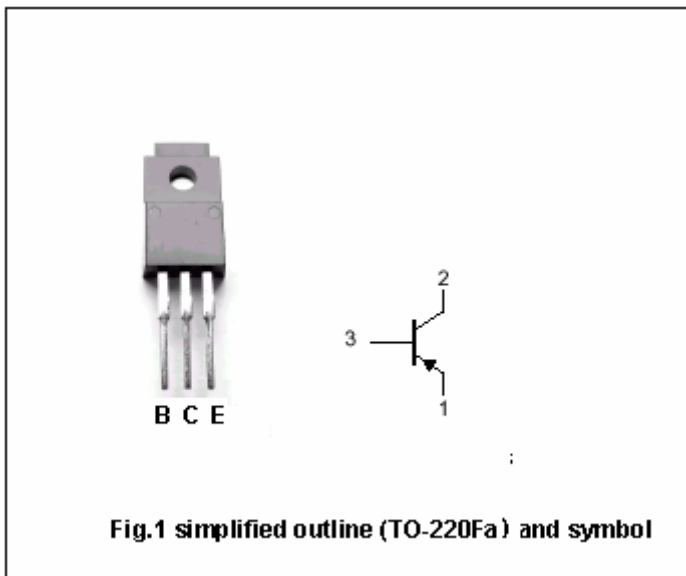
2SB1370

DESCRIPTION

- With TO-220Fa package
- $P_C=2W(T_a=25^\circ) / 30W(T_C=25^\circ)$
- Low collector saturation voltage
- Wide area of safe operation

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector
3	Base



Absolute maximum ratings( $T_a=25^\circ$ )

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	-60	V
$V_{CEO}$	Collector -emitter voltage	Open base	-60	V
$V_{EBO}$	Emitter-base voltage	Open collector	-5	V
$I_C$	Collector current		-3	A
$I_{CM}$	Collector current-peak		-6	A
$P_C$	Collector power dissipation	$T_a=25^\circ$	2.0	W
		$T_C=25^\circ$	30	
$T_j$	Junction temperature		150	$^\circ$
$T_{stg}$	Storage temperature		-55~150	$^\circ$

## Silicon PNP Power Transistors

## 2SB1370

## CHARACTERISTICS

T<sub>j</sub>=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =-1mA; I <sub>B</sub> =0	-60			V
V <sub>(BR)CBO</sub>	Collector-base breakdown voltage	I <sub>C</sub> =-50μA; I <sub>E</sub> =0	-60			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =-50μA; I <sub>C</sub> =0	-5			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =-2A; I <sub>B</sub> =-0.2A			-1.5	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =-2A; I <sub>B</sub> =-0.2A			-1.5	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =-60V; I <sub>E</sub> =0			-10	μA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =-4V; I <sub>C</sub> =0			-10	μA
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =-0.5A; V <sub>CE</sub> =-5V	100		320	
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =-0.5A; V <sub>CE</sub> =-5V		15		MHz
C <sub>OB</sub>	Collector output capacitance	f=1MHz; V <sub>CB</sub> =10V		80		pF

Silicon PNP Power Transistors

2SB1370

PACKAGE OUTLINE

